

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

MCH6431 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1= $42m\Omega$ (typ.)
- · 4V drive
- · Halogen free compliance
- · Protection diode in

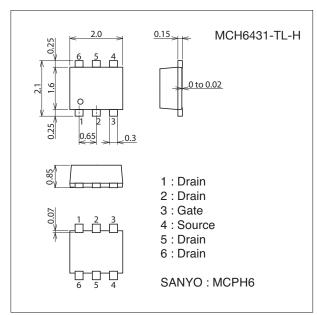
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	20	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7022A-009



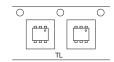
Product & Package Information

• Package : MCPH6

• JEITA, JEDEC : SC-88, SC-70-6, SOT-363

• Minimum Packing Quantity : 3,000 pcs./reel

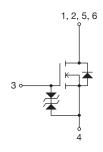
Packing Type: TL



Marking



Electrical Connection

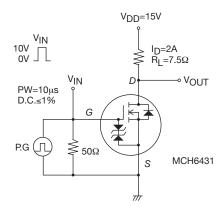


MCH6431

Electrical Characteristics at Ta=25°C

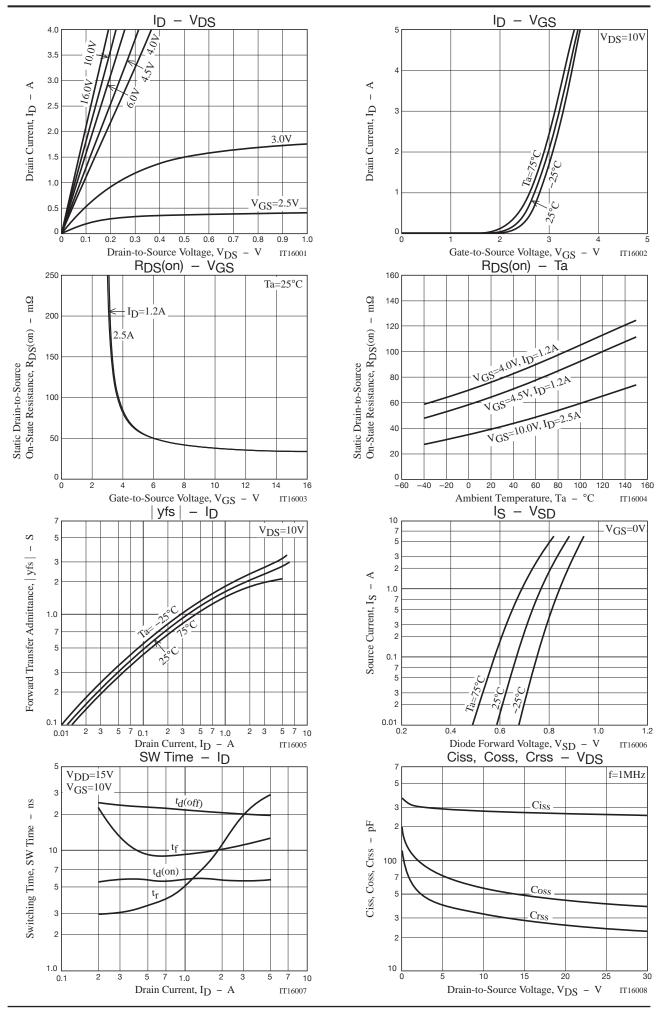
Parameter	Cump b al	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =2.5A		2.2		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =2.5A, V _{GS} =10V		42	55	mΩ	
	R _{DS} (on)2	I _D =1.2A, V _{GS} =4.5V		65	91	mΩ	
	R _{DS} (on)3	I _D =1.2A, V _{GS} =4V		78	109	mΩ	
Input Capacitance	Ciss			280		рF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		60		pF	
Reverse Transfer Capacitance	Crss			30		pF	
Turn-ON Delay Time	t _d (on)			5.7		ns	
Rise Time	t _r	One are difficult Total Circuit		11		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		21		ns	
Fall Time	tf			10		ns	
Total Gate Charge	Qg			5.6		nC	
Gate-to-Source Charge	Qgs	V _{DS} =15V, V _{GS} =10V, I _D =5A		1.2		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		0.8		nC	
Diode Forward Voltage	V _{SD}	I _S =5A, V _{GS} =0V		0.85	1.2	V	

Switching Time Test Circuit

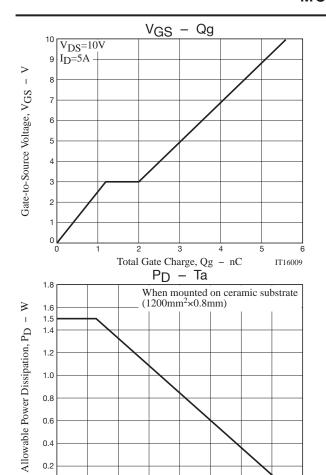


Ordering Information

Device	Package	Shipping	memo	
MCH6431-TL-H MCPH6		3,000pcs./reel	Pb Free and Halogen Free	



MCH6431



80

Ambient Temperature, Ta - °C

100

140

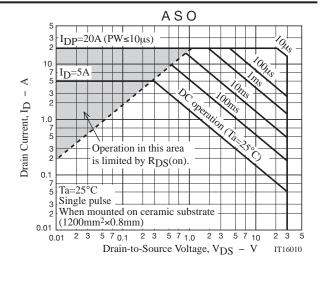
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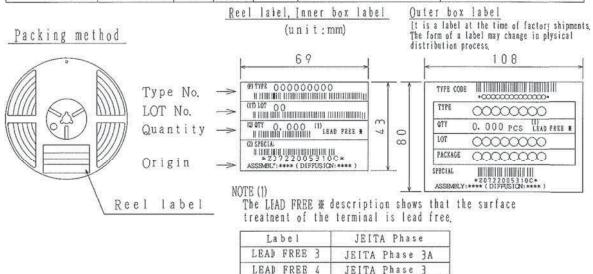


Taping Specification

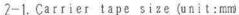
MCH6431-TL-H

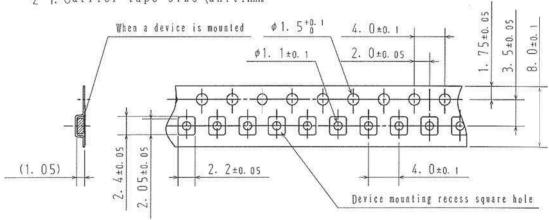
1. Packing Format

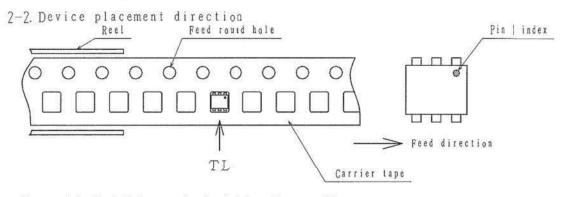
Package Name Carrier Tape Type	Carrier Tape	Maximum Number of devices contained (yes)			Packing format		
	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)		
MCPH6	MCP4	3, 000	15, 000	90, 000	5 reels contained Dimensions:mm(external)	6 inner boxes contained Dimensions:mm(external)	
					183×72×185	440×195×210	



2. Taping configuration





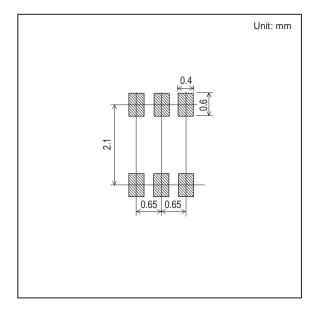


Those with pin 1 index on the feed hole side ·····TL

Outline Drawing

MCH6431-TL-H

Land Pattern Example



Note on usage: Since the MCH6431 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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